

ABSTRACT OF THE DISCLOSURE

A method is provided for tuning (i.e. modifying, changing) the impedance of semiconductor components or devices using a focused heating source. The method may be exploited for finely tuning the impedance of semiconductor components or devices, by modifying the dopant profile of a region of low dopant concentration (i.e. increasing the dopant concentration) by diffusion of dopants from adjacent regions of higher dopant concentration through the melting action of a focused heating source, for example a laser. The present invention is in particular directed to the use of lasers in relation to circuits for the creation of conductive links and pathways where none existed before. The present invention more particularly relates to a means wherein impedance modification (i.e. trimming or tuning) may advantageously be carried out as a function of the location of one or more conductive bridge(s) along the length of a gap region.